



2SA965 TRANSISTOR (PNP)

FEATURES

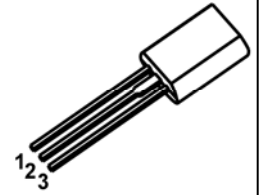
- Complementary to 2SC2235
- Power Amplifier Applications

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol Para	meter	Value	Unit
V _{CB0}	Collector-Base Voltage	-120	V
V _{CEO}	Collector-Emitter Voltage	-120	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-0.8	A
P _C	Collector Power Dissipation	900	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	139	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

TO – 92L

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA, I _E =0	-120			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-120			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-120V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =100mA	80		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-1	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V, I _C =-0.5A			-1	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			40	pF
Transition frequency	f _T	V _{CE} =-5V, I _C =-100mA		120		MHz

CLASSIFICATION OF h_{FE}

RANK O		Y
RANGE	80-160	120-240